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# P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)	
- 60	5.7 at V <sub>GS</sub> = - 10 V	- 110	142 nC	
- 00	6.5 at V <sub>GS</sub> = - 6 V	- 110		

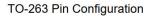
## **FEATURES**

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested



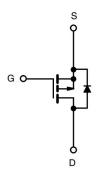
## **APPLICATIONS**

· Load Switch





Top View



P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	- 60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 110	^	
$(T_J = 150  ^{\circ}C)$	T <sub>C</sub> = 100 °C		- 73		
Pulsed Drain Current		I <sub>DM</sub>	- 330	Α	
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 70		
Single Pulse Avalanche Energy <sup>a</sup>	L = 0.1 IIII	E <sub>AS</sub>	253	mJ	
Power Dissipation	T <sub>C</sub> = 25 °C °	В	298	W	
	T <sub>A</sub> = 25 °C b	P <sub>D</sub>	2.05		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	UNIT	
Junction-to-Ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	60	°C/W	
Junction-to-Case		R <sub>thJC</sub>	0.42	C/VV	

#### Notes

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR4 material).
- c. See SOA curve for voltage derating.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V	
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T	I <sub>D</sub> = - 250 μA		48		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 230 μA		- 5.2			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	٧	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
	Town	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1	- 1 - 10 μA	
Zero Gate Voltage Drain Current	DSS	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 110			Α	
Drain-Source On-State Resistance <sup>a</sup>	R	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A		5.7	7.5	mΩ	
	R <sub>DS(on)</sub>	$V_{GS} = -6 \text{ V}, I_D = -30 \text{ A}$		6.5	8.6		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 30 A		80		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			6180		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1003			
Reverse Transfer Capacitance	C <sub>rss</sub>			20			
Total Gate Charge	Qg			142			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -30 \text{ A}$		16		nC	
Gate-Drain Charge	$Q_{gd}$			23			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		8		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			20			
Rise Time	t <sub>r</sub>	$V_{DD} = -30 \text{ V}, I_D = -30 \text{ A},$		85		- ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	VGEN = - 10 V, $R_g = 2.5 \Omega$		140			
Fall Time	t <sub>f</sub>			116			
<b>Drain-Source Body Diode Characteristic</b>	S						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 110	A	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 330		
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 1 A			- 1.2	٧	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			95		ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	30 A di/dt 100 A/vo T 25 °C		59		nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = -30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		29			
Reverse Recovery Rise Time	t <sub>b</sub>	_		16		ns	

#### Notes

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

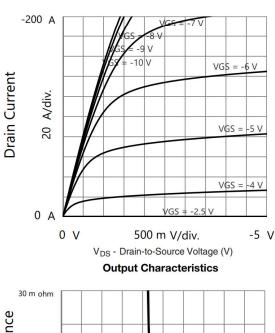
a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.

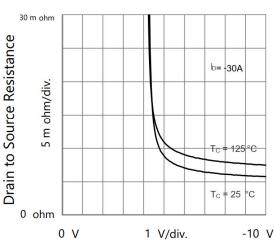
b. Guaranteed by design, not subject to production testing.



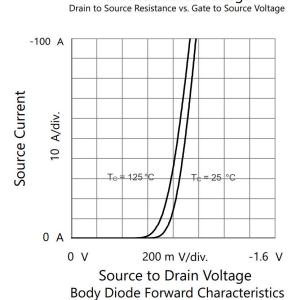


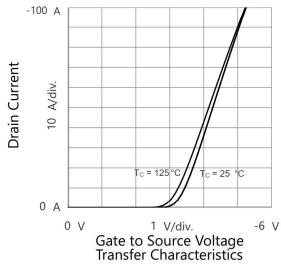
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

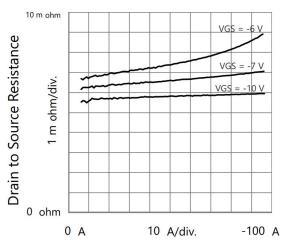




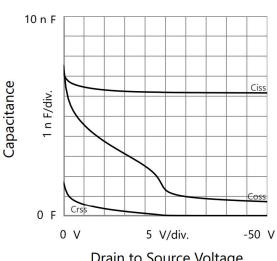
Gate to Source Voltage







Drain Current
Drain to Source Resistance vs. Drain Current

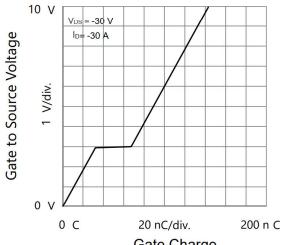


Drain to Source Voltage Capacitances

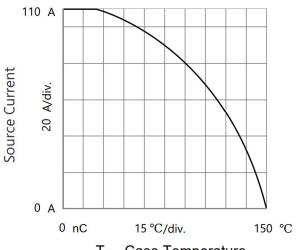




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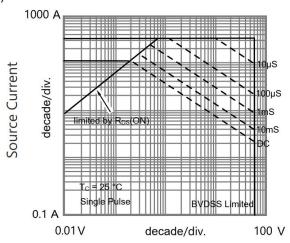


Gate Charge
Gate to Source Voltage vs. GateCharge

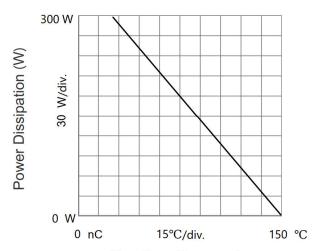


T<sub>C</sub> - Case Temperature

Current Derating

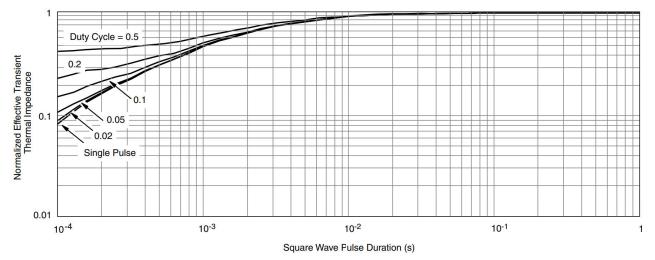


Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T<sub>C</sub> - Case Temperature

Current Derating



Normalized Thermal Transient Impedance, Junction-to-Case



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